

	Hits	Search Text	DBs
8	33	((low\$3k or dielectric or silicon\$5nitride or SiON or (low\$4 near16 dielectric)) same ((upper\$3 near5 portion) or sacrific\$4 or cap\$2 or SiO\$2 or (silicon near5 \$3oxide)) same (convert\$4 or (plasma\$4 near9 (ash\$5 or treat\$6 or oxidation or oxidiz\$5)))) and ((low\$3k or dielectric or silicon\$5nitride or SiON or (low\$4 near16 dielectric)) same (heat\$9 or bak\$4 or anneal\$4)) and ((pattern\$6 or photolithograph\$8 or lithograph\$6) same (via or trench or dual\$9damascene)) and via and trench and ((out\$5gas\$5 or dissipat\$4 or eliminat\$4 or rid\$4 or dispos\$4 or exhaust\$4) same (volatile or contaminat\$4 or poison\$4) same (substrate or dielectric or low\$3k or wafer))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	67	((low\$3k or dielectric or silicon\$5nitride or SiON or (low\$4 near16 dielectric)) same (upper\$3 or surface or top or sacrific\$4 or cap\$2 or SiO\$2 or (silicon near5 \$3oxide)) same (convert\$4 or (plasma\$4 near9 (ash\$5 or treat\$6 or oxidation or oxidi\$5)))) and ((low\$3k or dielectric or silicon\$5nitride or SiON or (low\$4 near16 dielectric)) same (heat\$9 or bak\$4 or anneal\$4)) and ((pattern\$6 or photolithograph\$8 or lithograph\$6) same (via or trench or dual\$9damascene)) and via and trench and ((out\$5gas\$5 or dissipat\$4 or eliminat\$4 or rid\$4 or dispos\$4 or exhaust\$4) same (volatile or contaminat\$4 or poison\$4) same (substrate or dielectric or low\$3k or wafer))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB